R. Fabian Pease Nanofabrication











Nanofabrication

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An Approach to Microminiature Printed Systems

D. A. BUCK K. R. SHOULDERS

THE DAY is rapidly drawing near when digital computers will no longer be made by assembling thousands of individually manufactured parts into plugin assemblies and then completing their interconnection with back-panel wiring. An alternative to this method is one in which an entire computer or a large part of a computer is made in a single process. Vacuum deposition of electrodes onto blocks of pure silicon or germanium and the subsequent diffusion of the electrode material into the block to form junctions a most promising method. The successful development of this method would llow large numbers of transistors and all of their interconnecting wiring to be made in one operation. Vacuum deposition of magnetic materials and conductors to form coincident-current magnetic-core memory planes is a second promising method that will allow an entire memory to be made in one operation. The vacuum deposition of superconductive switching and memory circuits is a third method that will make possible the printing of an entire computer. The authors feel sure that the most significant milestone in computer component technology will be the announcement by one or more firms, in perhaps 2 years, that all of the technical problems of building a printed system

1958

have been solved, and that one of their engineers with his vacuum system car make a digital computer in an hour.

All three methods mentioned, as well as others not mentioned, involve vacuum deposition through a mask. A cleaned glass substrate or a semiconducting surface is placed in a vacuum system, and the air pumped out until the residual pressure is below 10^{-4} atmosphere. A piece ometal near to the substrate is then heated and atoms of that metal evaporate. Some condense onto the substrate, forming a thin film. Between the source of atom and the substrate a mask is placed to in

This paper is part of a panel discussion on "Th Impending Revolution in Computer Technology.

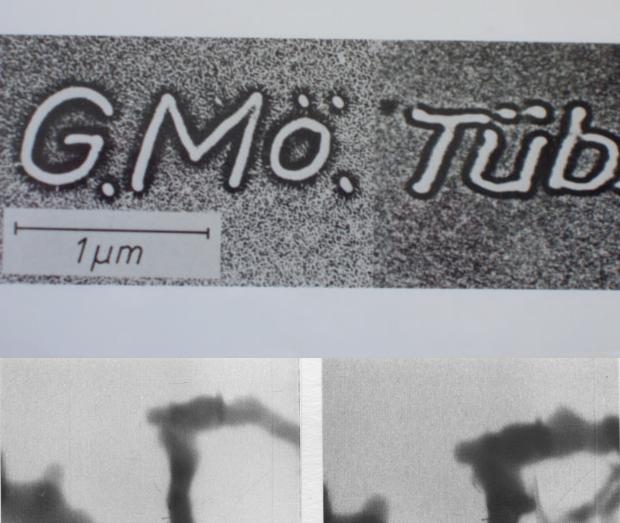
D. A. BUCK (deceased) was with Massachusett Institute of Technology, Cambridge, Mass.

K. R. SHOULDERS is with Stanford Research Institute, Menlo Park, Culif.

The work reported here was supported in part b the U. S. Navy (Bureau of Ships) and in part by th U. S. Army (Signal Corps), the U. S. Air Forc (Office of Scientific Research and Developmen Command), and the U. S. Navy (Office of Nava Research).

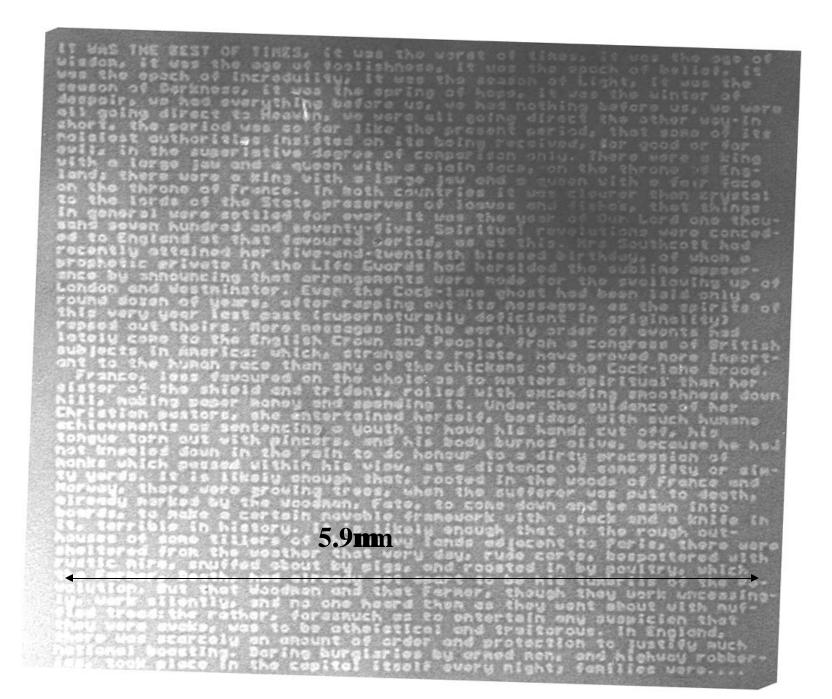
Ioellenstedt and Speidel, 1960 one of the first examples of Nanowriting' using a modified ansmission electron microscope to eform a collodion film and then hadowing with evaporated metal G. Mollenstedt and R. Speidel, hysikalische Blatter, February 960).

ease, 1963 SEM 5 (Tx-mode), ree-standing contamination Structures'





Tom Newman, Ann Marshall, Stanford, 1985



CALIFORNIA INSTITUTE OF TECHNOLOGY

CHARLES C. LAURITSEN LABORATORY OF HIGH ENERGY PHYSICS

November 19, 1985

Dr. Thomas H. Newman 452 McCullough Building Stanford University Stanford, CA 94305

Dear Dr. Newman:

Congratulations to you and your colleagues. You have certainly satisfied my idea of what I wanted to give a prize for. Others have apparently made as small or smaller marks, but no one tried to print an entire page. And on a 512 x 512 dot printer! Each dot is only about 60 atoms on a side. I can't quite manage to imagine the square 1/160 mm on a side onto which all that is printed. It would be 20 times too small on a side to see with the naked eye. Only ten wave lengths of light. The entire Encyclopaedia Brittanica, perhaps 50,000 to 100,000 pages of your size would be on less than 2 mm on a side - the head of a small plain pin.

Your description of the square silicon nitride windows was a bit incomplete. How big are the windows? Is each window a page, or (less probably?) a letter? Can application to computers be far behind?

As promised long ago, I am enclosing a check for \$1,000 for your accomplishment.

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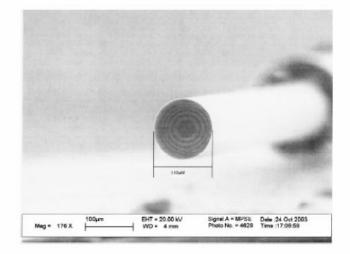
Richard P. Feynman

RPF;ht encl.

RICHARD P. FEYNMAN GWENETH FEYNMAN 797-1262 2475 BOULDER RD. ALTADENA, CA 91001	16-66/120 760 DATE 1/01.17/985
One thousand and	Neurman s1000 - L'mario Dollars
BANKOFAMERICA" ALTADEM BRANCH 0591 2016 DOX 577 ALTADENA, CA 81001	Richard P. Jeyman

Examples of More Flexible Tools

- High resolution EBL systems with tilt stages
 - Lithography performed at the end of an optical fiber in an SEM by P. S. Kelkar *et al.* J. Vac. Sci. Technol. A **22**, 743 (2004)



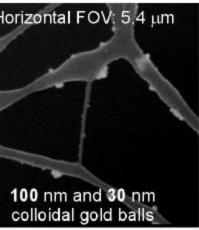
- High resolution dedicated EBL systems with variable pressure chambers
 - Benefits already being explored for photomask CD metrology. For example, D.C. Joy Proc. SPIE Int. Soc. Opt. Eng. 5375, 10 (2004)
 - Simplify patterning of bulk insulators, SFIL templates, etc.



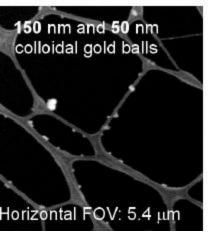
For Icm²/s EBL at 22nm we need distributed-axis electron optics DIFA (Groves, Leica and Pickard, Stanford Univ)

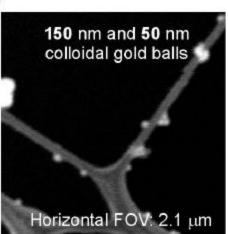
High Resolution (below 50 nm) Imaging (10 kV, 2 orbits)

0 nm and 30 nm colloidal gold balls:



nm and 50 nm colloidal gold balls:

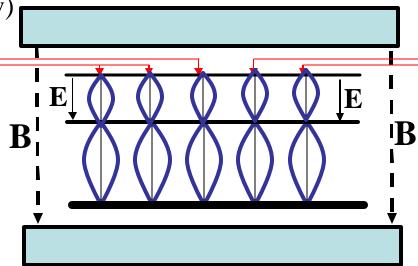


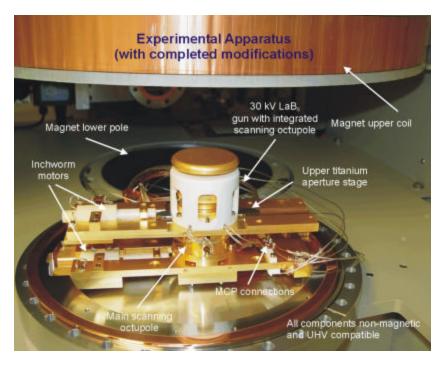


100 nm and 30 nm

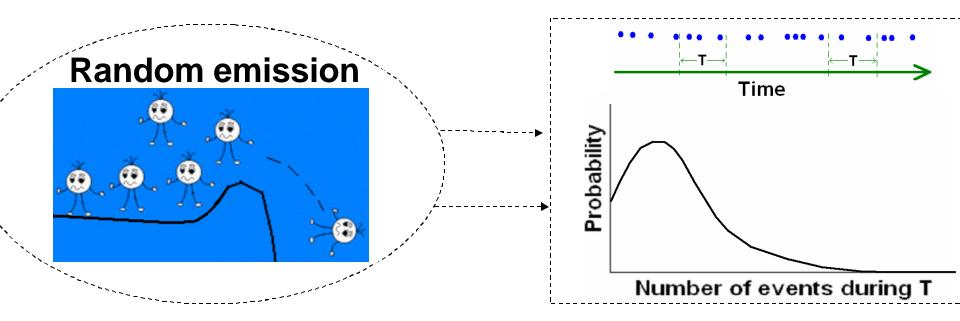
colloidal gold balls

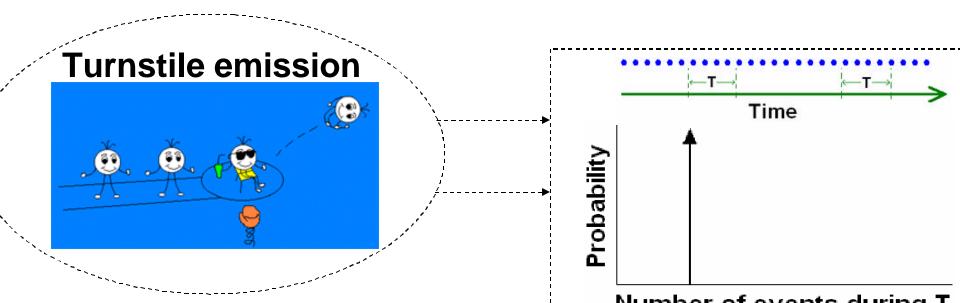
Horizontal FOV: 2.1 um





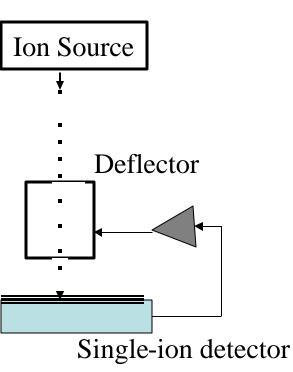
Shot noise



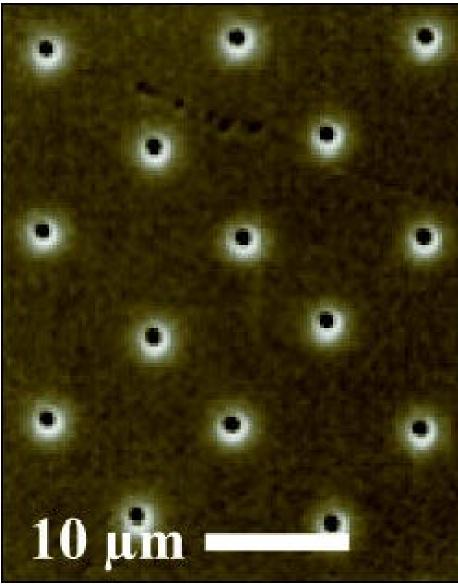


Opportunity: Do something about the shot noise: realize the single-quantum feature

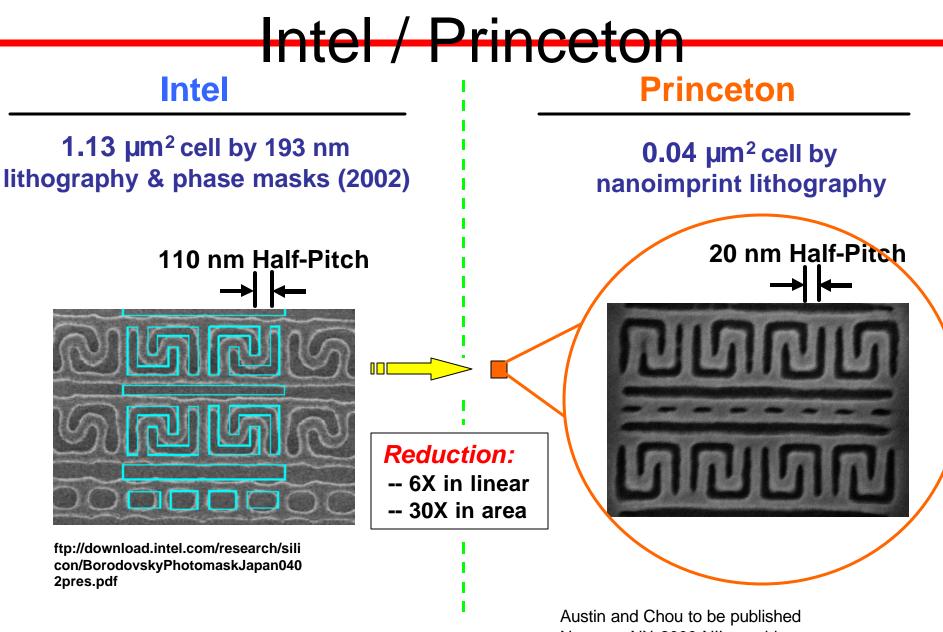
FIB exposure: moved 'beam position' after monitoring 1 ion landing.



Europhysics News (2004) Vol. 35 No. 5 Ion tracks – a new route to nanotechnology



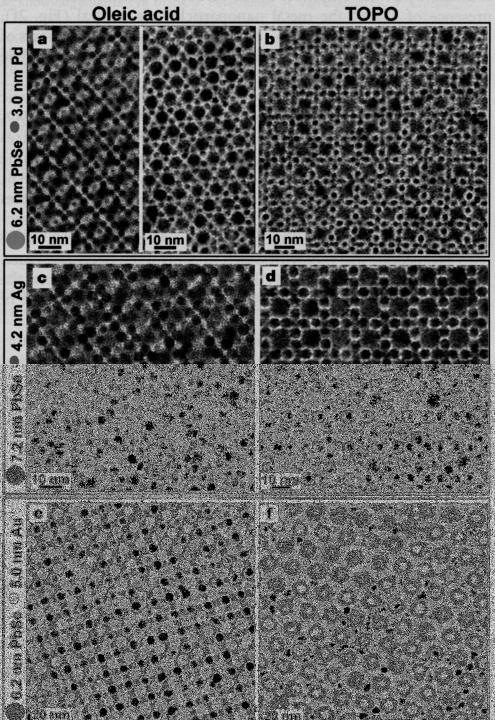




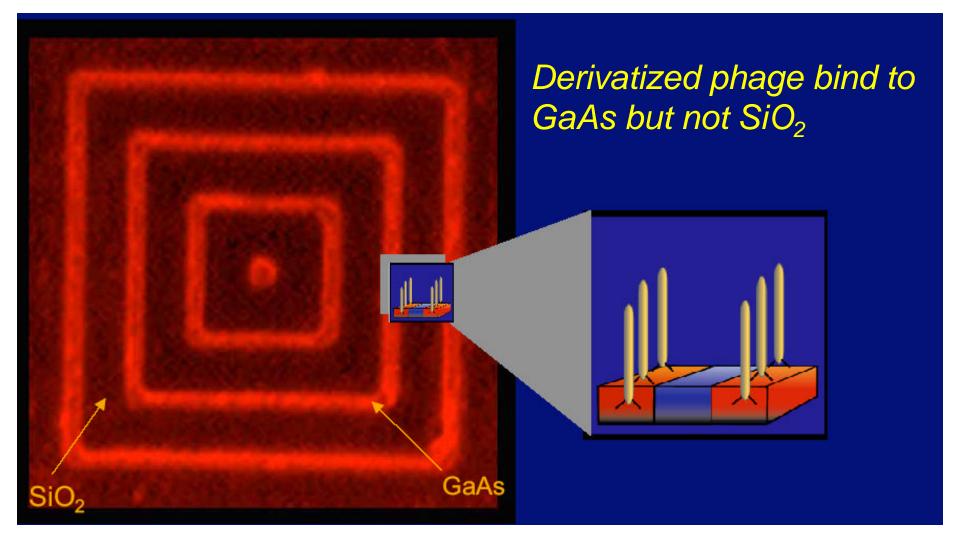
Nanonex NX-2000 NIL machines Nanonex NXR-2010 resist

- Shevchenko et al.
- Nature,439, 5Jan2006, p.55

Binary Nanoscale Superlattices

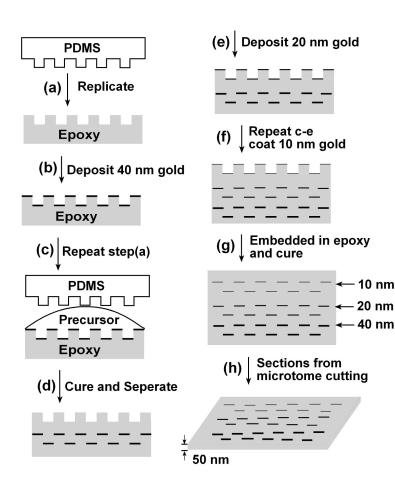


Binding Agents Are Highly Specific

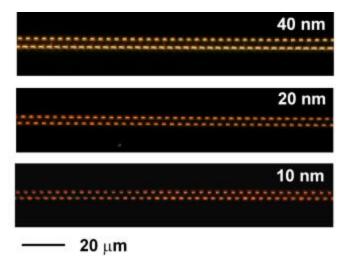




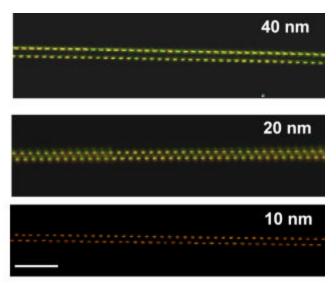
Sectioning as a route to nanostructures...



100 nm section



50 nm section



Unpublished results

Conclusions

- Very low volume nanofabrication is well established,
- Manufacturing at the nanoscale presents major challenges: pattern generation, economic throughput, placement, assured freedom from defects,
- There are many opportunities for improvement. New ideas are continually emerging. They need a disciplined approach.